

Silicon Epitaxial Planar Diode

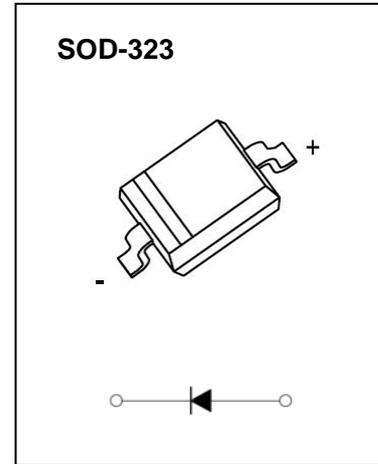
Low leakage switching diode

Features

- Plastic SMD package
- Low leakage current

Application

- Low leakage current applications in surface mounted circuits.



MARKING: JV

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	85	V
Continuous Reverse Voltage	V _R	75	V
Continuous Forward Current	I _F	200	mA
Repetitive Peak Forward Current	I _{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I _{FSM}	t = 1 μs	4
		t = 1 ms	1
		t = 1 s	0.5
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 65 to + 150	°C

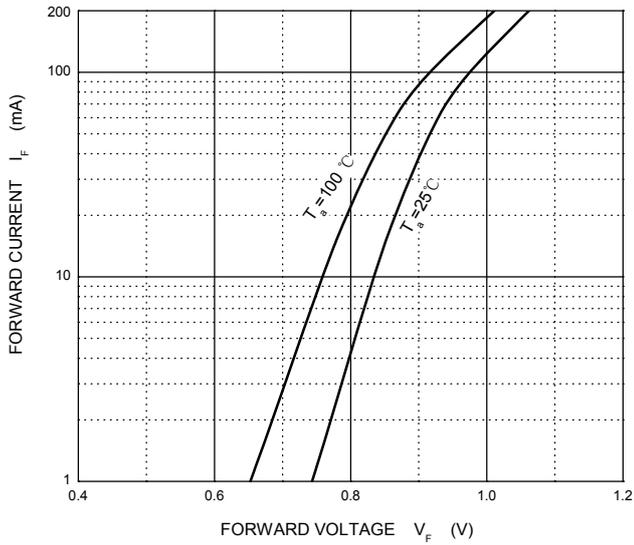
Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage	V _F	-	at I _F = 1 mA	0.9
			at I _F = 10 mA	1
			at I _F = 50 mA	1.1
			at I _F = 150 mA	1.25
Reverse Current	I _R	-	at V _R = 75 V	5
			at V _R = 75 V, T _j = 150 °C	80
Diode Capacitance	C _d	2	-	pF
Reverse Recovery Time	t _{rr}	-	3	μs
at I _F = I _R = 10 mA, R _L = 100 Ω, i _{rr} = 0.1 I _R				

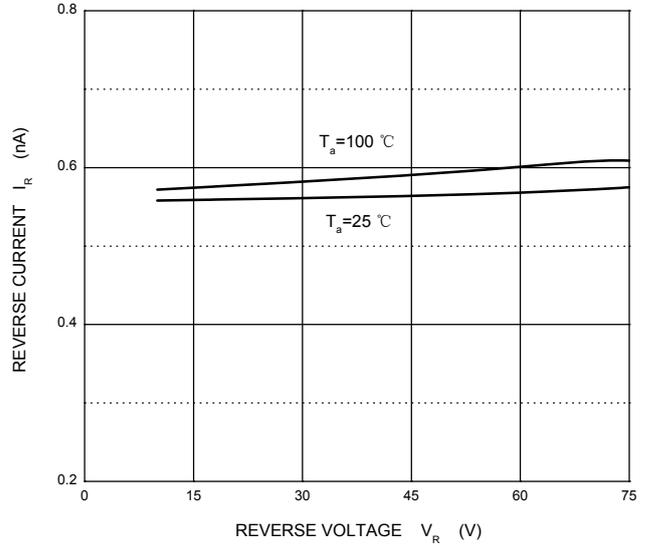


Typical Characteristics

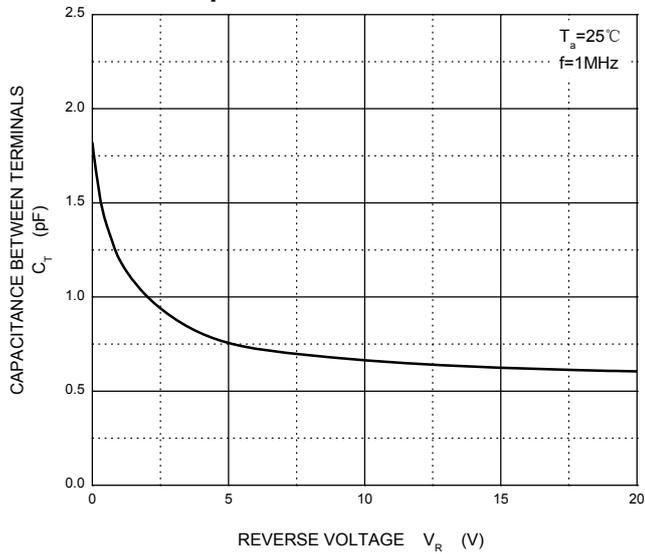
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

